

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	3.0Ω @ V <sub>GS</sub> = 4.5V	240mA
	6.0Ω @ V <sub>GS</sub> = 1.8V	180mA

## Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## Applications

- DC-DC Converters
- Power Management Functions

## Features and Benefits

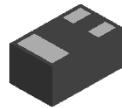
- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package, 0.4mm Maximum Package Height
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

## Mechanical Data

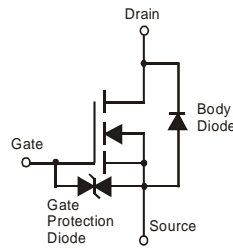
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.001 grams (Approximate)



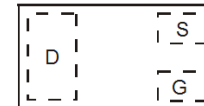
X2-DFN1006-3



Bottom View



Equivalent Circuit



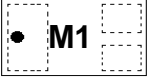

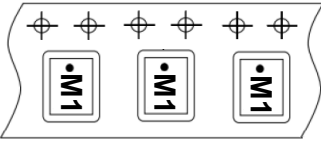
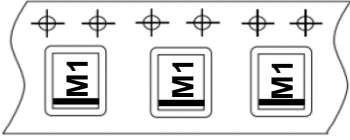
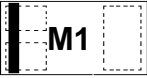
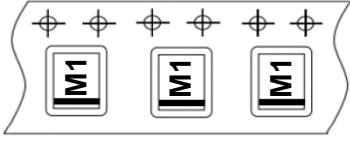
Top View

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN26D0UFB4-7	X2-DFN1006-3	3,000/Tape & Reel
DMN26D0UFB4-7B	X2-DFN1006-3	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**

<p><b>DMN26D0UFB4-7</b></p>	<div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: center;">  <p>Top View Dot Denotes Drain Side</p> </div> <div style="text-align: center;"> <p>From date code 1527 (YYWW), this changes to:</p>  <p>Top View Bar Denotes Gate and Source Side</p> </div> </div> <div style="display: flex; justify-content: space-around; margin-top: 20px;">   </div>
<p><b>DMN26D0UFB4-7B</b></p>	<div style="text-align: center; margin-bottom: 20px;">  <p>Top View Bar Denotes Gate and Source Side</p> </div> <div style="display: flex; justify-content: space-around; margin-bottom: 20px;">  </div> <p style="text-align: right;">M1 = Part Marking Code</p>

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±10	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	240	mA
		T <sub>A</sub> = +70°C		190	
Continuous Drain Current (Note 5) V <sub>GS</sub> = 1.8V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	180	mA
		T <sub>A</sub> = +70°C		140	
Pulsed Drain Current - t <sub>p</sub> = 10µs			I <sub>DM</sub>	805	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5) @T <sub>A</sub> = +25°C	P <sub>D</sub>	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	357	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Note: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 100μA
Zero Gate Voltage Drain Current @ T <sub>C</sub> = +25°C	I <sub>DSS</sub>	—	—	500	nA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±1 ±100	μA nA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.6	—	0.9	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.8	3.0	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100mA V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 50mA V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 20mA V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA
		—	2.5	4.0		
		—	3.4	6.0		
		—	4.7	10.0		
Forward Transconductance	Y <sub>fs</sub>	180	242	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.1A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	—	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	14.1	28.2	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	2.9	5.8	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	1.6	3.2	pF	
<b>SWITCHING CHARACTERISTICS (Note 7)</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.8	—	ns	V <sub>GS</sub> = 4.5V, V <sub>DD</sub> = 10V I <sub>D</sub> = 200mA, R <sub>G</sub> = 2.0Ω
Rise Time	t <sub>R</sub>	—	7.9	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	13.4	—		
Fall Time	t <sub>F</sub>	—	15.2	—		

Notes: 6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

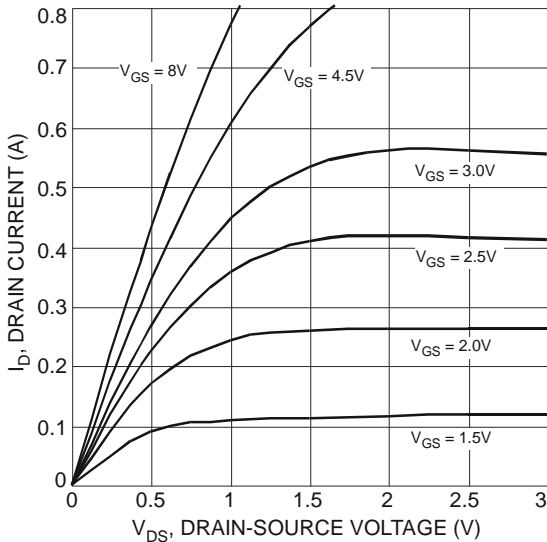


Fig. 1 Typical Output Characteristic

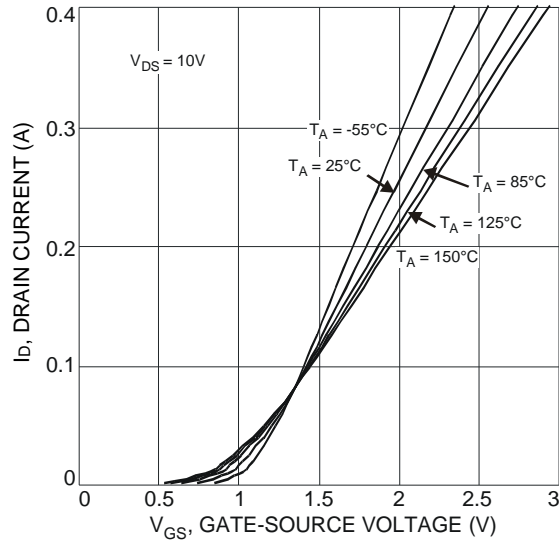


Fig. 2 Typical Transfer Characteristic

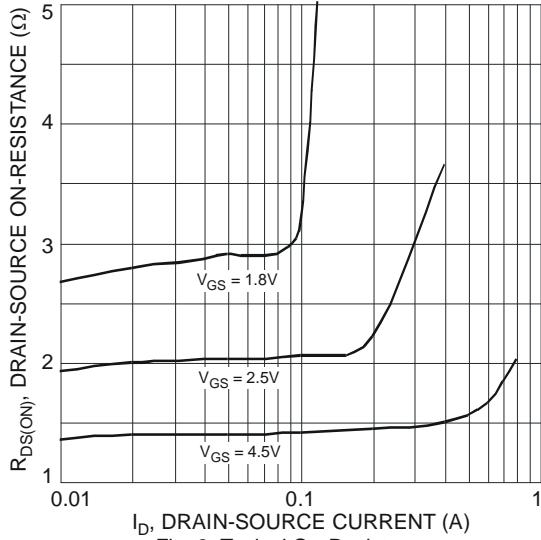


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

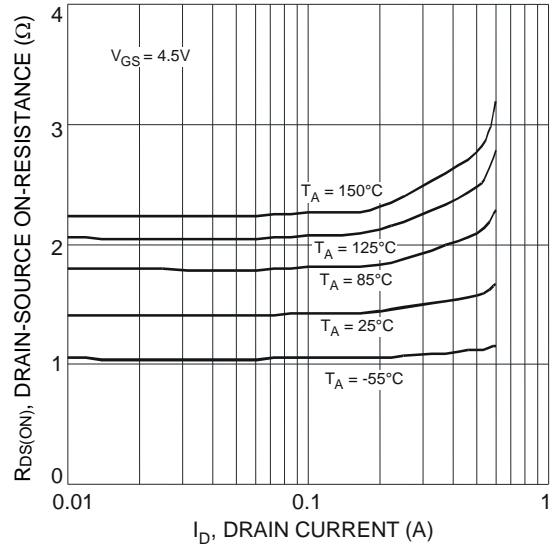


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

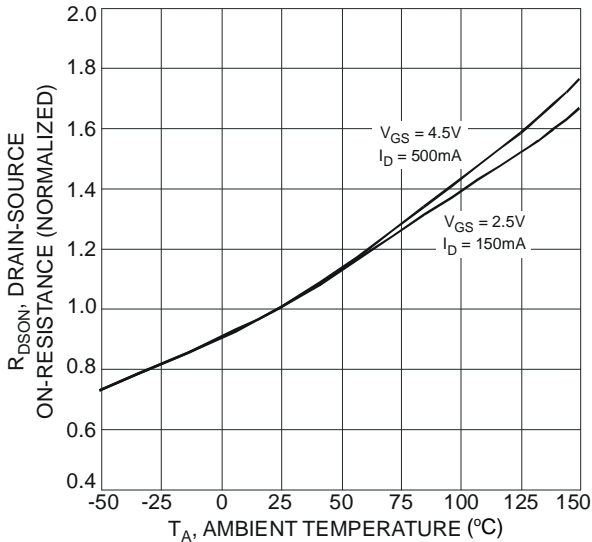


Fig. 5 On-Resistance Variation with Temperature

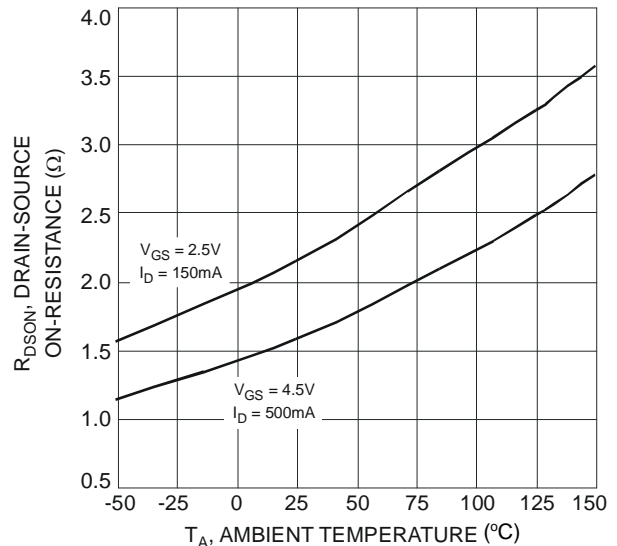


Fig. 6 On-Resistance Variation with Temperature

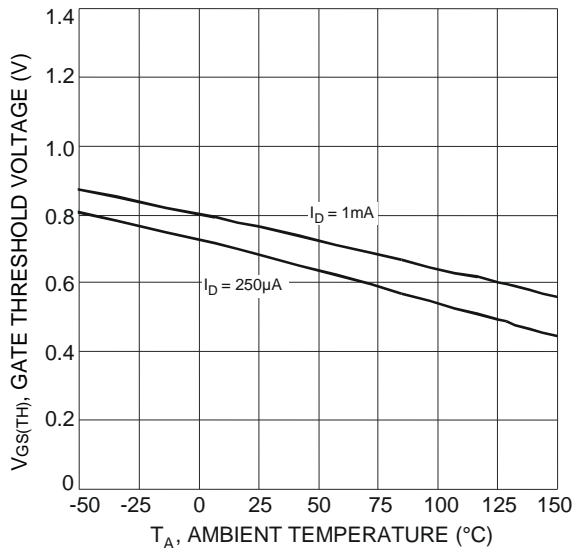


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

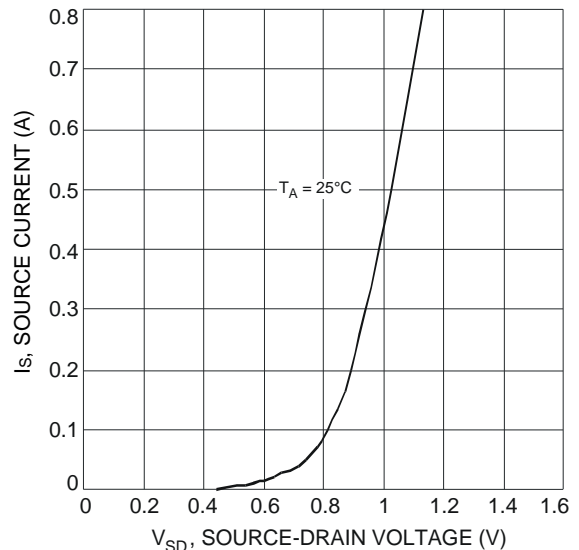


Fig. 8 Diode Forward Voltage vs. Current

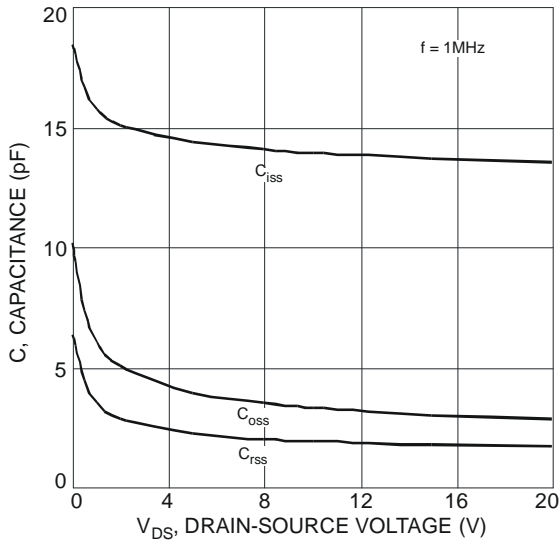


Fig. 9 Typical Total Capacitance

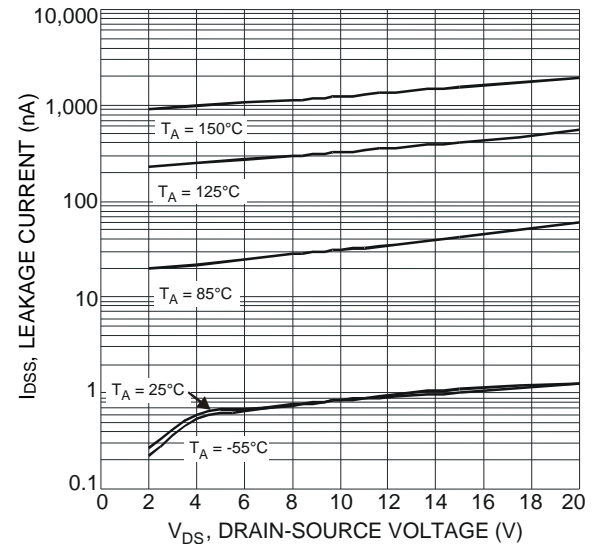


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

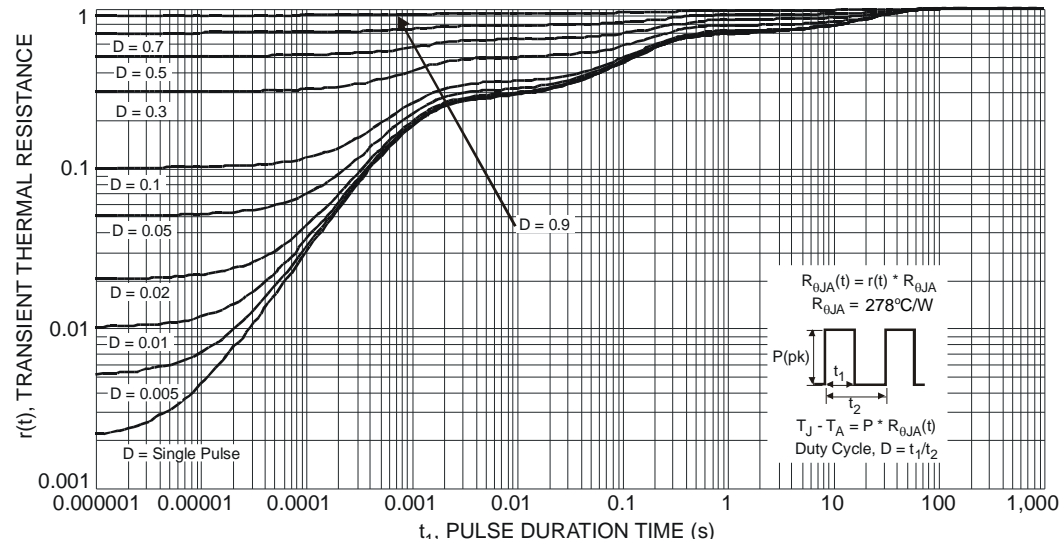
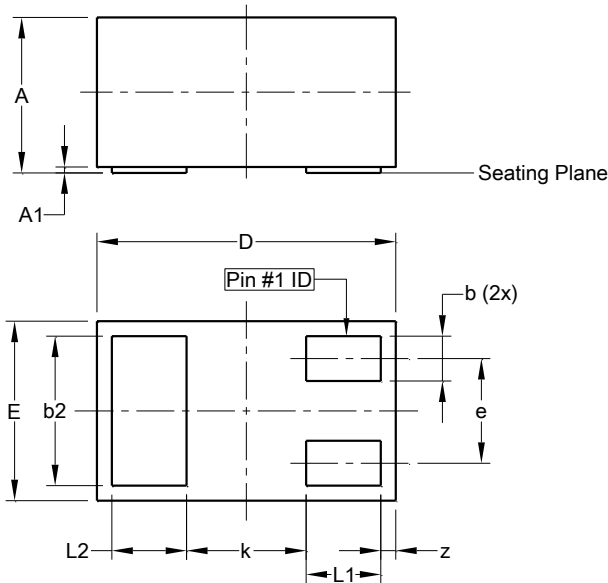


Fig. 11 Transient Thermal Response

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**X2-DFN1006-3**

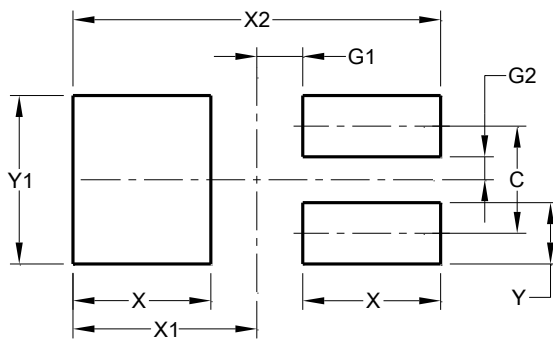


X2-DFN1006-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
k	—	—	0.40
z	0.02	0.08	0.05
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**X2-DFN1006-3**



Dimensions	Value (in mm)
C	0.350
G1	0.150
G2	0.075
X	0.450
X1	0.600
X2	1.200
Y	0.200
Y1	0.550

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